Session Title:	[TD2] Plasma/Etch Simulation
Session Date:	November 21 (Tue.), 2023
Session Time:	10:20-11:30
Session Room:	Room D (Grand Ballroom 3, 2F)
Session Chair:	Prof. Chinwook Chung (Hanyang Univ., Korea)

[TD2-1] 10:20-10:40

Dependence of Gas Mixing Ratio and Pressure on Optimal Condition for Abundant $O(^1D)$ Surface Flux in O_2/Ar Inductively Coupled Plasmas

Cheongbin Cheon (Pusan Nat'l Univ., Korea), Sanghyun Jo, Ho Jun Kim (Hanyang Univ., Korea), and Hae June Lee (Pusan Nat'l Univ., Korea)

[TD2-2] 10:40-11:00

Predictable Process Simulation Platform for Next-Generation Plasma Oxide Etching Processes

Jae-Hyeong Park, Hae-Sung You, Jeon-Su Chae, Hyeong-Jun Mun (Jeonbuk Nat'l Univ., Korea), Kook-Hyun Yoon, Sung-Sik Shin, Dong-Hun Yu (Kyung Won Tech. Inc., Korea), Won-Seok Chang, Deuk-Chul Kwon, JungSik Yoon (KFE, Korea), and Yeon-Ho Im (Jeonbuk Nat'l Univ., Korea)

[TD2-3] [Invited] 11:00-11:30

Etching Mechanism of Amorphous Hydrogenated Silicon Nitride by Hydrogen Fluoride

Khabib Khumaini, Yewon Kim, Romel Hidayat, Hye-Lee Kim (Sejong Univ., Korea), Byungchul Cho, Sangjoon Park (Wonik IPS, Korea), and Won-Jun Lee (Sejong Univ., Korea)